

Title (en)

METHOD FOR TRANSFERRING A SINGLE-CRYSTAL SILICON THIN FILM

Title (de)

VERFAHREN ZUR ÜBERTRAGUNG EINER SILIZIUMEINKRISTALL-DÜNNSCICHT

Title (fr)

PROCEDE DE TRANSFERT D'UNE COUCHE MINCE DE SILICIUM MONOCRISTALLIN

Publication

EP 2586055 A1 20130501 (FR)

Application

EP 11727692 A 20110621

Priority

- FR 1054969 A 20100622
- EP 2011060380 W 20110621

Abstract (en)

[origin: WO2011161122A1] The invention relates to a method for transferring a single-crystal silicon thin film (3) from a donor substrate (1) made of single-crystal silicon, in which: the implantation conditions are such that the thickness of the thin film (3) is less than 10 µm; and the thickness of a polymer layer (5) for gluing the thin film to a receiving substrate is less than a critical threshold defined in accordance with the energy and amount of the implantation, said critical threshold being less than or equal to the smallest of the following two quantities: 500 nm; and the thickness of the future thin film.

IPC 8 full level

H01L 21/762 (2006.01)

CPC (source: EP US)

B32B 38/0008 (2013.01 - US); **C23C 14/0005** (2013.01 - EP US); **C23C 14/48** (2013.01 - EP US); **H01L 21/76254** (2013.01 - EP US); **Y02P 20/582** (2015.11 - EP US)

Citation (search report)

See references of WO 2011161122A1

Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

DOCDB simple family (publication)

FR 2961515 A1 201111223; **FR 2961515 B1 20120824**; CN 103098196 A 20130508; EP 2586055 A1 20130501; JP 2013533622 A 20130822; US 2013092320 A1 20130418; US 8906780 B2 20141209; WO 2011161122 A1 201111229

DOCDB simple family (application)

FR 1054969 A 20100622; CN 201180030915 A 20110621; EP 11727692 A 20110621; EP 2011060380 W 20110621; JP 2013515872 A 20110621; US 201113805796 A 20110621